

Table 2: Absolute Ratings (limiting values)

Symbol	Parameter		Value	Unit
$V_{\text{DRM}}/$ V_{RRM}	Repetitive peak off-state voltage	$T_j = 125\text{ }^{\circ}\text{C}$	700	V
$I_{\text{T(RMS)}}$	RMS on-state current full cycle sine wave 50 to 60 Hz, no heat sink	$T_{\text{amb}} = 40\text{ }^{\circ}\text{C}$	1.5	A
	RMS on-state current full cycle sine wave 50 to 60 Hz, TO-220AB package	$T_{\text{case}} = 105\text{ }^{\circ}\text{C}$	6	A
I_{TSM}	Non repetitive surge peak on-state current T_j initial = $25\text{ }^{\circ}\text{C}$, full cycle sine wave	$t_p = 20\text{ms}$	45	A
		$t_p = 16.7\text{ms}$	50	A
I^2t	Thermal constraint for fuse selection	$t_p = 10\text{ms}$	11	A^2s
di/dt	Non repetitive on-state current critical rate of rise $I_G = 10\text{mA}$ ($t_R < 100\text{ns}$)	Rate period $> 1\text{mn}$	100	$\text{A}/\mu\text{s}$
V_{PP}	Non repetitive line peak pulse voltage (see note 1)		2	kV
T_{stg}	Storage temperature range		- 40 to + 150	$^{\circ}\text{C}$
T_j	Operating junction temperature range		- 30 to + 125	$^{\circ}\text{C}$
T_l	Maximum lead soldering temperature during 10s		260	$^{\circ}\text{C}$

Note 1: according to test described by IEC61000-4-5 standard and figure 3.

Table 3: Gate Characteristics (maximum values)

Symbol	Parameter	Value	Unit
P_G (AV)	Average gate power dissipation	0.1	W
P_{GM}	Peak gate power dissipation ($t_p = 20\mu\text{s}$)	10	W
I_{GM}	Peak gate current ($t_p = 20\mu\text{s}$)	1	A

Table 4: Thermal Resistances

Symbol	Parameter	Value	Unit
$R_{\text{th(j-a)}}$	Junction to ambient TO-220AB / TO-220FPAB	60	$^{\circ}\text{C}/\text{W}$
$R_{\text{th(j-a)}}$	Junction to ambient $I^2\text{PAK}$	65	
$R_{\text{th(j-a)}}$	Junction to ambient $D^2\text{PAK}$ soldered on 1 cm^2 copper pad	45	
$R_{\text{th(j-c)}}$	Junction to case for full cycle sine wave conduction (TO-220AB)	2.5	$^{\circ}\text{C}/\text{W}$
$R_{\text{th(j-c)}}$	Junction to case for full cycle sine wave conduction (TO-220FPAB)	3.5	

Table 5: Parameter Description

Parameter Symbol	Parameter description
I_{GT}	Gate triggering current
V_{GT}	Gate triggering voltage
V_{GD}	Non triggering voltage
I_H	Holding current
I_L	Latching current
V_{TM}	On state voltage
V_{T0}	On state characteristic threshold voltage
R_d	On state characteristic dynamic resistance
I_{DRM} / I_{RRM}	Forward or reverse leakage current
dV/dt	Static pin OUT voltage rise
$(dI/dt)_c$	Turn off current rate of decay
V_{CL}	Avalanche voltage at turn off

Table 6: Electrical Characteristics

For either positive or negative polarity of pin OUT voltage respect to pin COM voltage

Symbol	Test conditions			Value	Unit
I_{GT}	$V_{OUT} = 12V$ (DC) $R_L = 33\Omega$	$T_j = 25^\circ C$	MAX.	10	mA
V_{GT}	$V_{OUT} = 12V$ (DC) $R_L = 33\Omega$	$T_j = 25^\circ C$	MAX.	1.5	V
V_{GD}	$V_{OUT} = V_{DRM}$ $R_L = 3.3\Omega$	$T_j = 125^\circ C$	MIN.	0.2	V
I_H	$I_{OUT} = 100mA$ Gate open	$T_j = 25^\circ C$	MAX.	25	mA
I_L	$I_G = 20mA$	$T_j = 25^\circ C$	MAX.	50	mA
V_{TM}	$I_{OUT} = 2.1A$ $t_p = 380\mu s$	$T_j = 25^\circ C$	MAX.	1.4	V
V_{TM}	$I_{OUT} = 8.5A$ $t_p = 380\mu s$	$T_j = 25^\circ C$	MAX.	1.7	V
V_{T0}		$T_j = 125^\circ C$	MAX.	0.9	V
R_d		$T_j = 125^\circ C$	MAX.	80	m Ω
I_{DRM} I_{RRM}	$V_{OUT} = V_{DRM}$	$T_j = 25^\circ C$	MAX.	20	μA
	$V_{OUT} = V_{RRM}$	$T_j = 125^\circ C$	MAX.	500	μA
dV/dt	$V_{OUT} = 600V$ gate open	$T_j = 125^\circ C$	MIN.	200	V/ μs
$(dI/dt)_c$	$(dI/dt)_c = 15V/\mu s$	$T_j = 125^\circ C$	MIN.	3	A/ms
$(dI/dt)_c$	$(dI/dt)_c = 15V/\mu s$ $I_{OUT} < 0$ $R_{gk} = 150\Omega$	$T_j = 125^\circ C$	MIN.	3.5	A/ms
V_{CL}	$I_{CL} = 1mA$ $t_p = 1ms$	$T_j = 25^\circ C$	TYP.	1100	V

AC LINE SWITCH BASIC APPLICATION

The ACST6-7S device is especially designed to drive medium power induction motors in refrigerators, dish washers, and tumble dryers.

Pin COM : Common drive reference, to be connected to the power line neutral

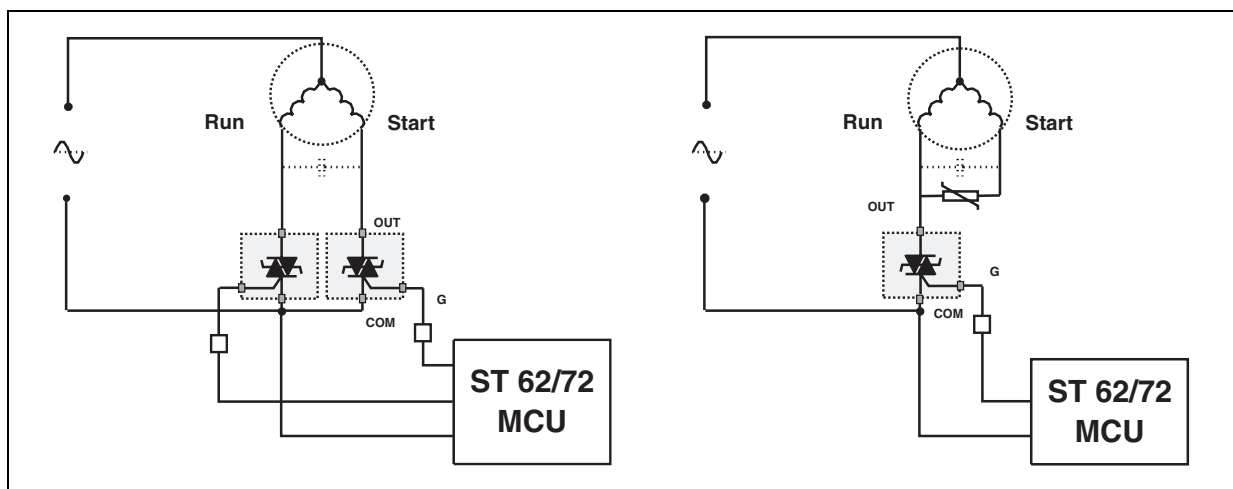
Pin G : Switch Gate input to be connected to the controller

Pin OUT : Switch Output to be connected to the load

When driven from a low voltage controller, the ACST switch is triggered with a negative gate current flowing out of the gate pin G. It can be directly driven by the controller through a resistor as shown on the typical application diagram. In appliance systems, the ACST6-7S switch intends to drive medium power load in ON / OFF full cycle or phase angle control mode.

Thanks to its thermal and turn-off commutation characteristics, the ACST6-7S switch is able to drive an inductive load up to 6A without a turn-off aid snubber circuit.

Figure 2: Typical Application Diagram



AC LINE TRANSIENT VOLTAGE RUGGEDNESS

The ACST6-7S switch is able to safely withstand the AC line transient voltages either by clamping the low energy spikes or by breaking over under high energy shocks.

The test circuit in figure 3 is representative of the ACST application and is used to test the ACST switch according to the IEC61000-4-5 standard conditions. Thanks to the load impedance, the ACST switch withstands voltage spikes up to 2 kV above the peak line voltage by breaking over safely. Such non-repetitive testing can be done 10 times on each AC line voltage polarity.

Figure 3: Overvoltage ruggedness test circuit for resistive and inductive loads according to IEC61000-4-5 standard $R = 10\Omega$, $L = 5\mu\text{H}$ & $V_{PP} = 2\text{kV}$

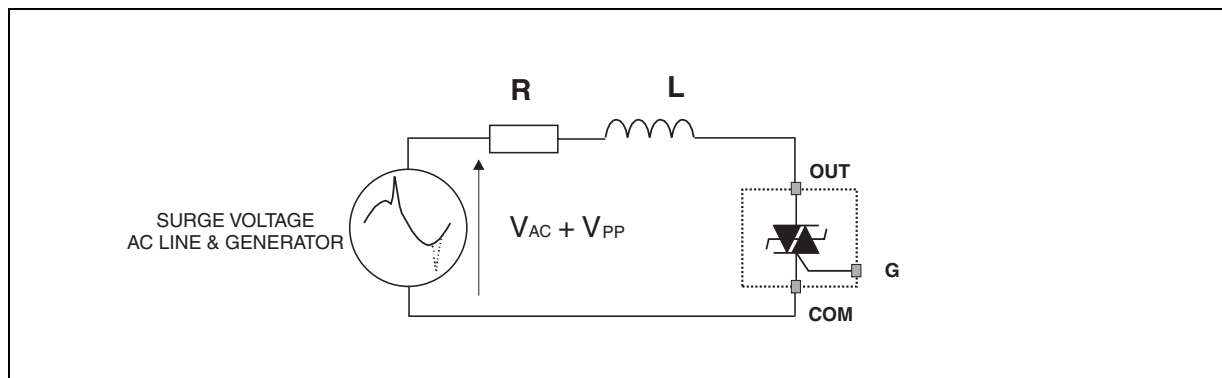


Figure 4: Maximum power dissipation versus RMS on-state current (full cycle)

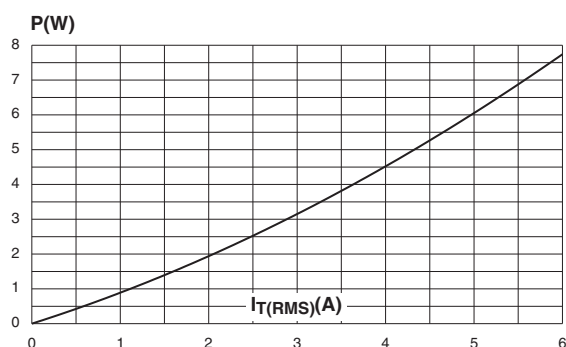


Figure 5: RMS on-state current versus case temperature (full cycle)

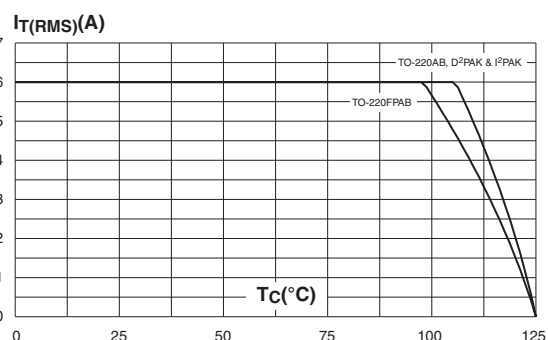


Figure 6: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35μm), full cycle

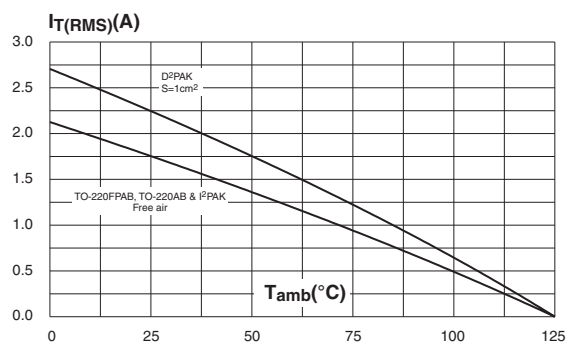


Figure 7: Relative variation of thermal impedance versus pulse duration

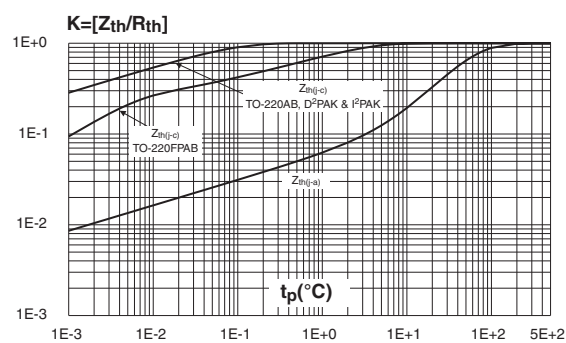


Figure 8: On-state characteristics (maximum values)

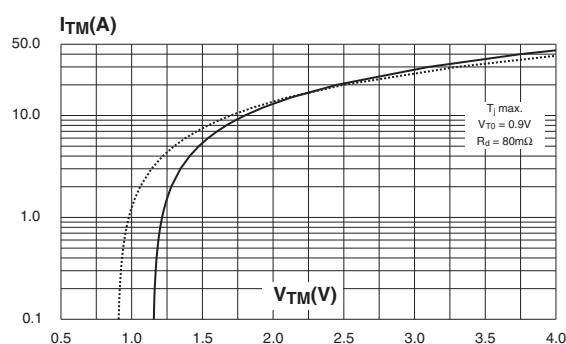


Figure 9: Surge peak on-state current versus number of cycles

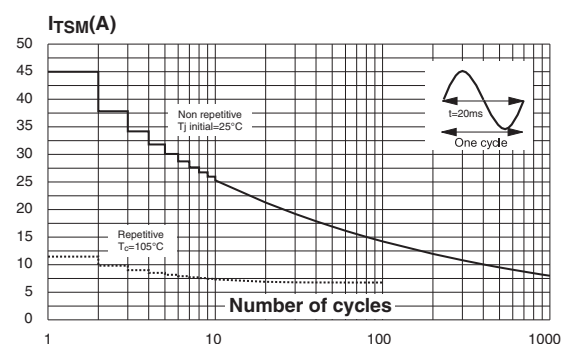


Figure 10: Non repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t

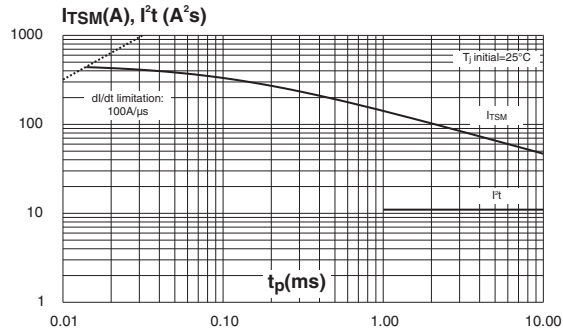


Figure 12: Relative variation of critical rate of decrease of main current versus reapplied $(dV/dt)_c$ (typical values)

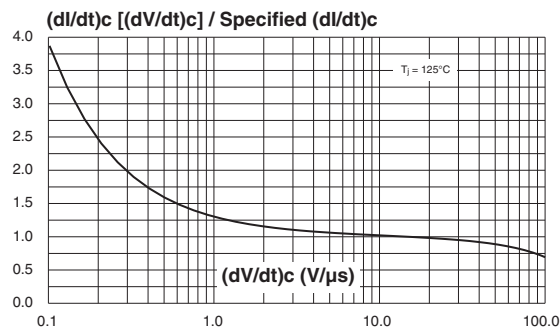


Figure 14: Relative variation of dV/dt immunity versus junction temperature for different values of gate to com resistance (gate open is the reference value)

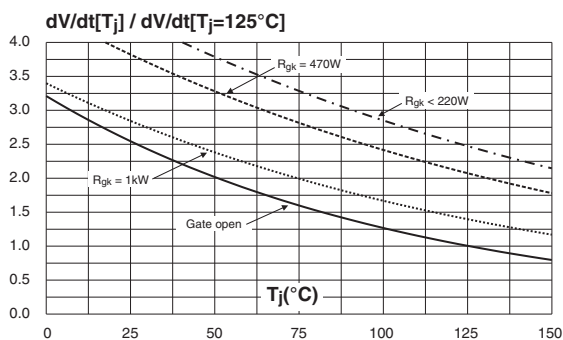


Figure 11: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)

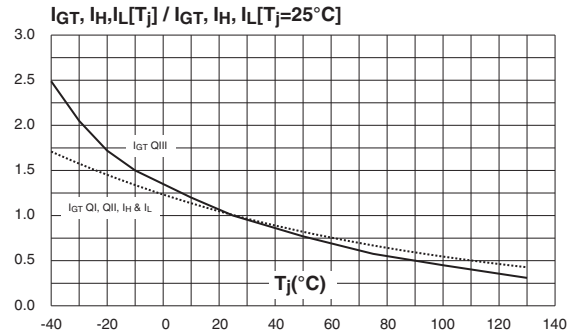


Figure 13: Relative variation of critical rate of decrease of main current versus junction temperature

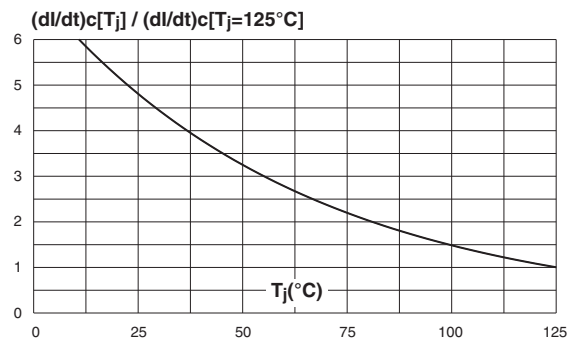


Figure 15: Thermal resistance junction to ambient versus copper surface under tab (printed circuit board FR4, copper thickness: $35\mu m$) (D^2PAK)

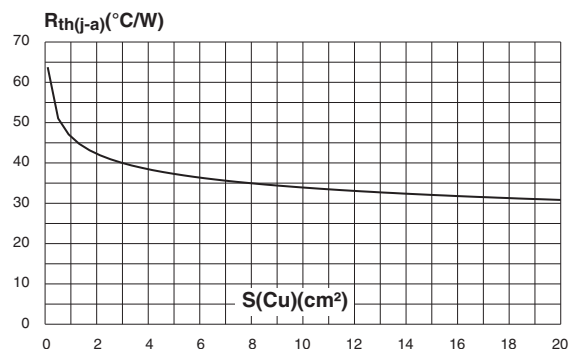


Figure 16: Ordering Information Scheme

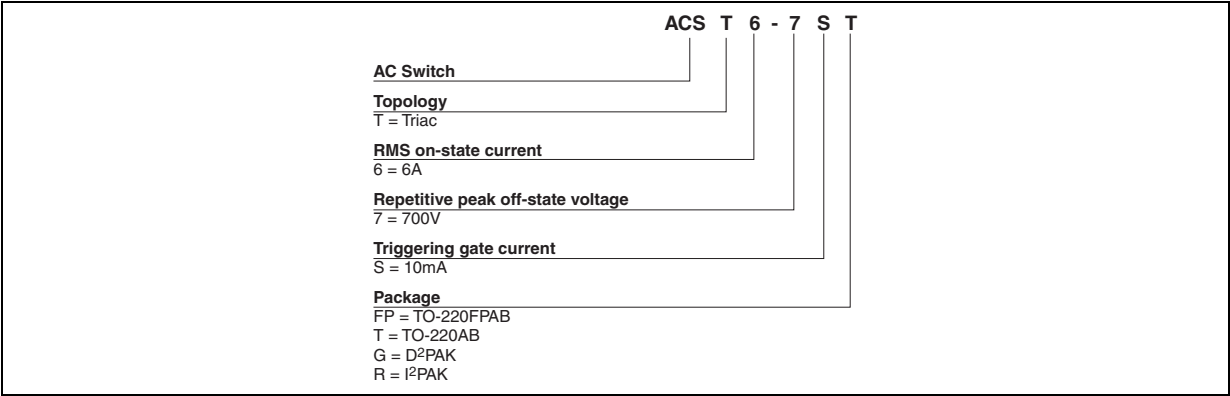


Figure 17: D²PAK Package Mechanical Data

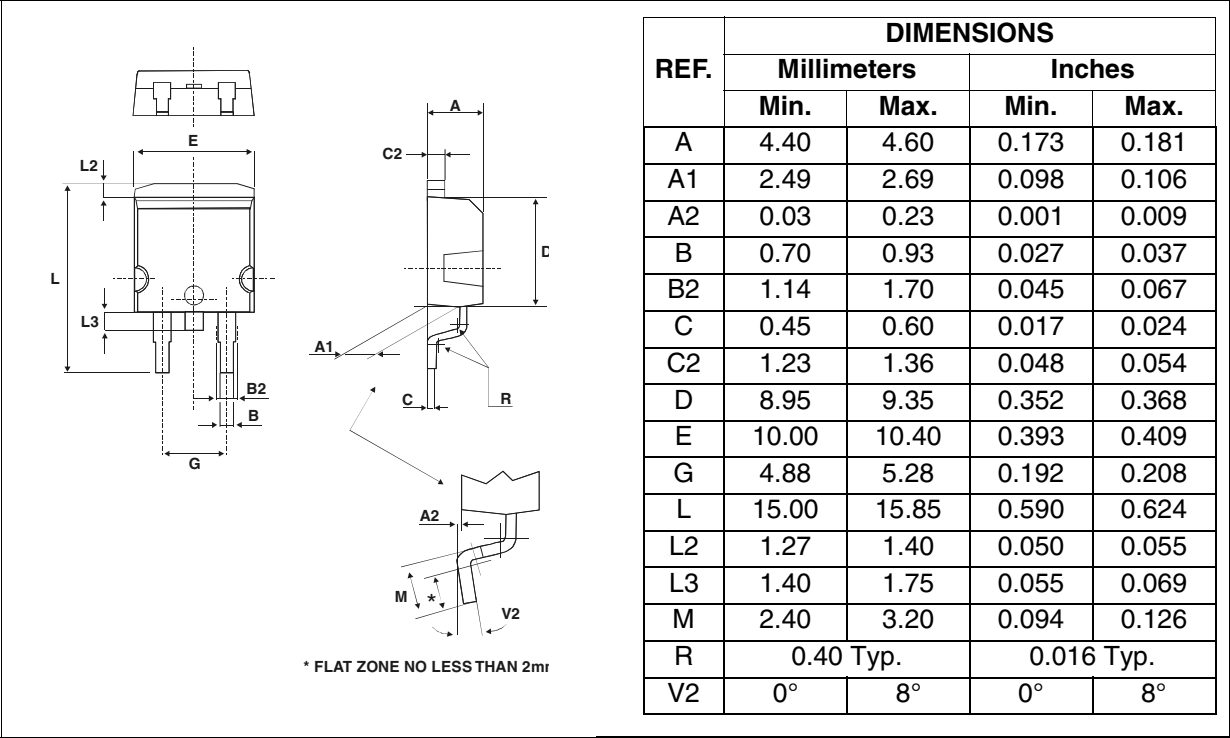


Figure 18: Foot Print Dimensions (in millimeters)

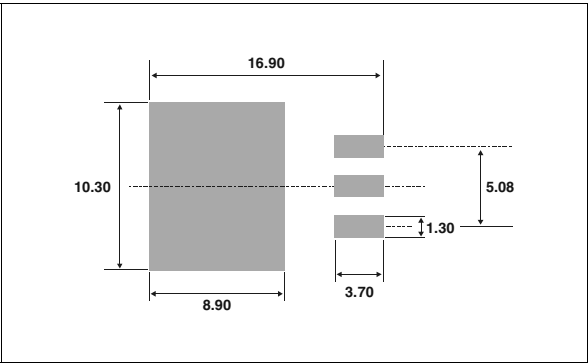


Figure 19: TO-220AB Package Mechanical Data

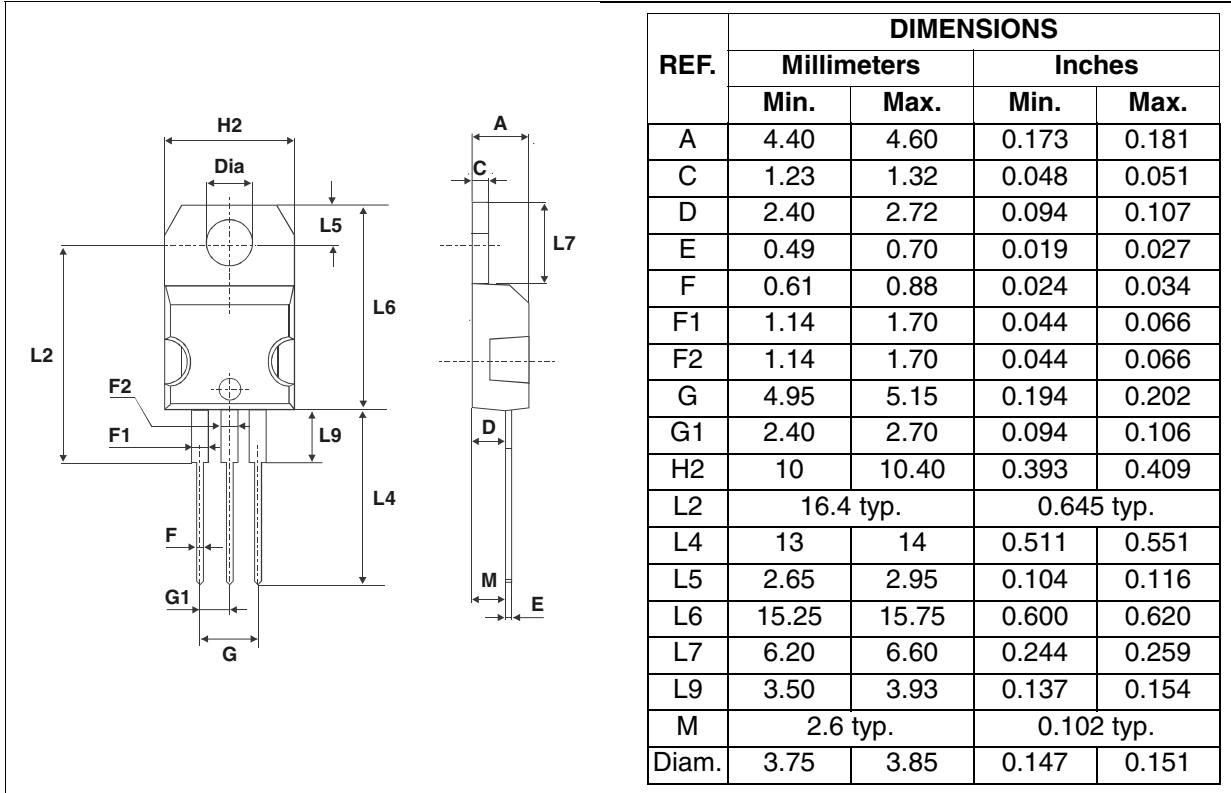


Figure 20: I²PAK Package Mechanical Data

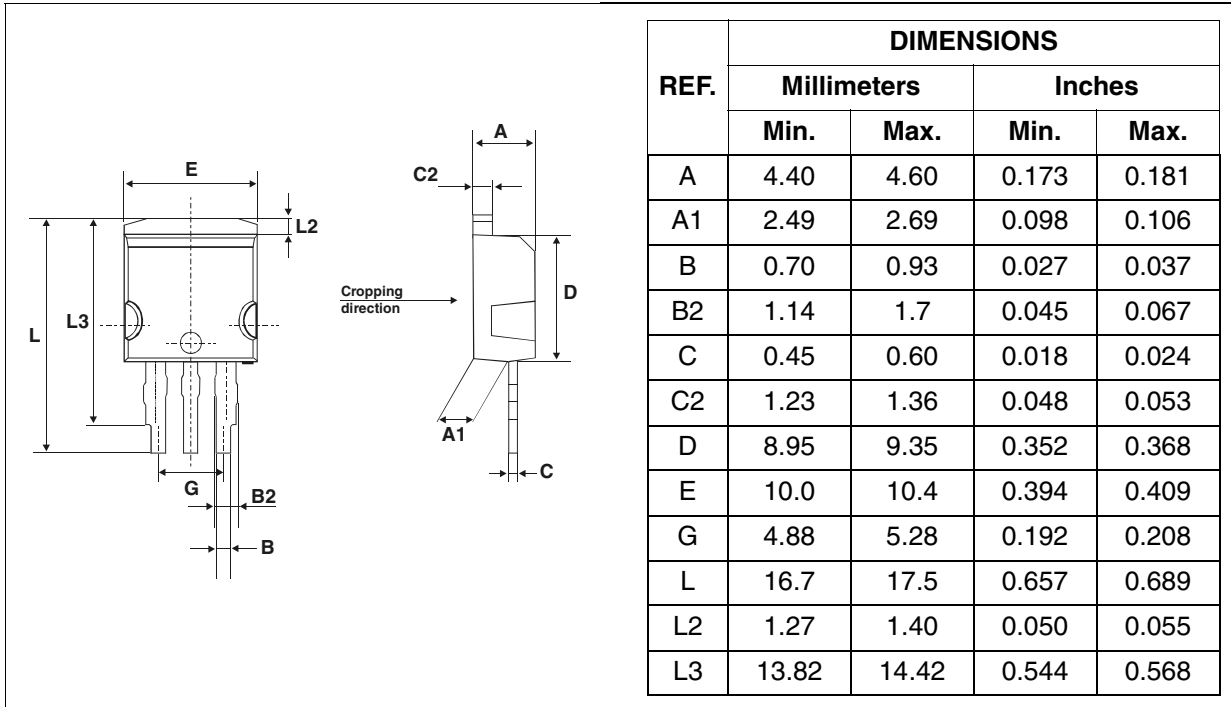


Figure 21: TO-220FPAB Package Mechanical Data

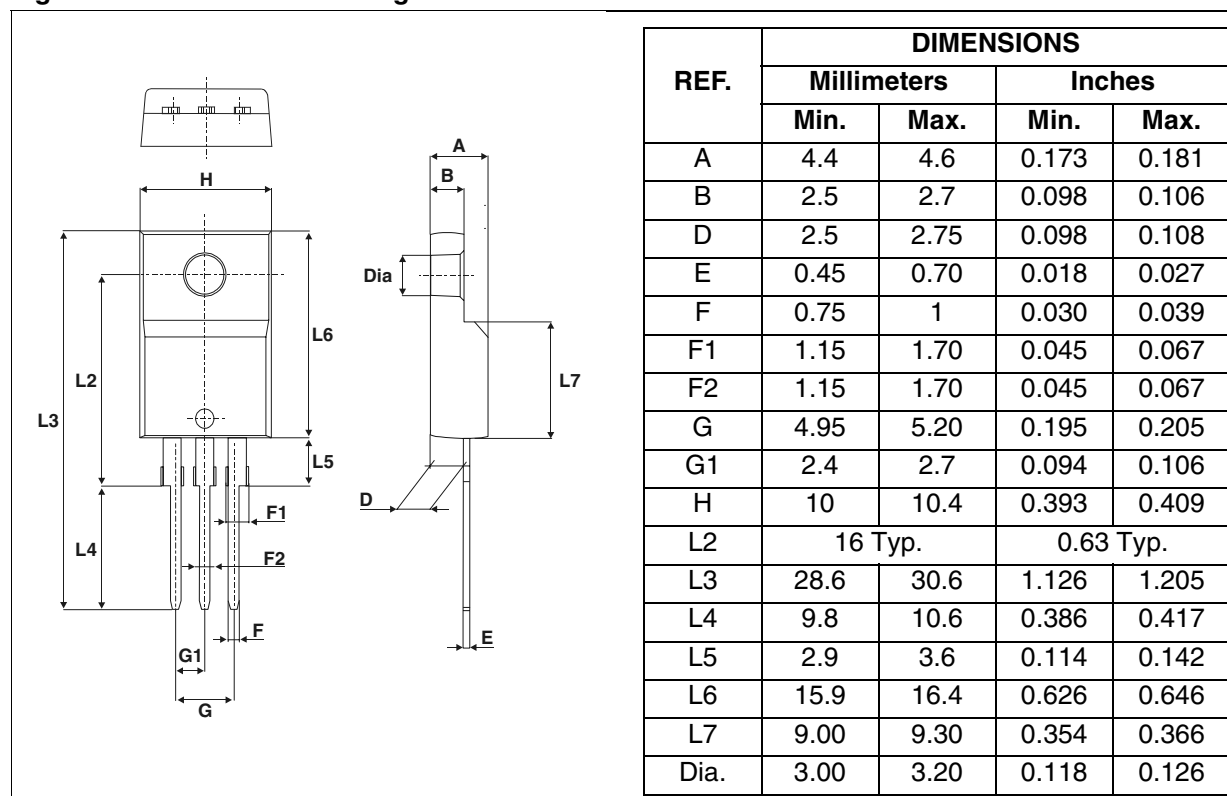


Table 7: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
ACST6-7ST	ACST67S	TO-220AB	2.3 g	50	Tube
ACST6-7SG	ACST67S	D ² PAK	1.5 g	50	Tube
ACST6-7SFP	ACST67S	TO-220FPAB	2.4 g	50	Tube
ACST6-7SR	ACST67S	I ² PAK	1.5 g	50	Tube

■ Epoxy meets UL94,V0

Table 8: Revision History

Date	Revision	Description of Changes
Jan-2002	7F	Last issue.
09-May-2005	8	Layout update. No content change.

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